NSN 5961-01-535-2194

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-535-2194 **Inclosure Material:** Plastic **Overall Length:** Between 0.180 inches and 0.200 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.145 inches and 0.165 inches **Mounting Method: Terminal Semiconductor Material:** Gallium arsenide Voltage Rating In Volts Per Characteristic: 30.0 breakdown voltage, collector-to-emitter, base open and 5.0 breakdown voltage, emitter to collector, base open **Current Rating Per Characteristic:** 0.55 microamperes service voltage **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius ambient air **Product Name:** Infrared selected npn silicon phootransistor **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0